## NSN 5962-01-395-6316

Memory Microcircuit - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5962-01-395-6316
Maximum Power Dissipation Rating:
1.2 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
End Application:
Pacer dawn
Features Provided:
Burn in, mil-std-883, class b and bipolar and electrostatic sensitive and hermetically sealed and monolithic and programmed and tested to
mil-std-883
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
20 input
Criticality Code Justification:
Feat
Current Rating Per Characteristic:
100.00 milliamperes reverse current, dc and 1.00 milliamperes reverse current, dc microamperes and 210.00 milliamperes reverse current,
dc absolute
Terminal Surface Treatment:
Solder
Product Name:
Microcircuit, digital, pal, wait state generator
Voltage Rating And Type Per Characteristic:
-1.5 volts input and 5.5 volts input and -0.5 volts power source and 7.0 volts power source
Time Rating Per Chacteristic:
20.00 nanoseconds input to output access
Memory Device Type:
Pal
Special Features:
Esd; altered item programmed from 67268 5962-8767101lx using pg639000-01 program; case size is gdip3-t24 or cdip4-t24
Test Data Document:
96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Quantity:
24 printed circuit

--

N/a

Shelf Life:

**Unit Of Measure:** 

## NSN 5962-01-395-6316

Memory Microcircuit - Page 2 of 2



Demilitarization:

No

Fiig:

A458a0